

Silicon PNP Power Transistors

2SB707 2SB708

DESCRIPTION

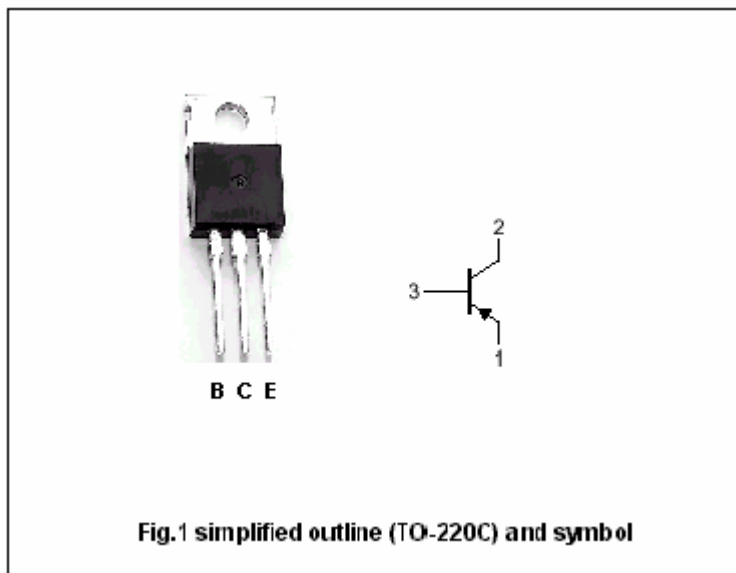
- With TO-220C package
- Complement to type 2SD568/569

APPLICATIONS

- For low frequency power amplifier
- low speed switching industrial use

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	2SB707	Open base	-60	V
		2SB708		-80	
V_{EBO}	Emitter-base voltage		Open collector	-7	V
I_C	Collector current			-7	A
I_{CM}	Collector current-peak			-15	A
I_B	Base current			-3.5	A
P_C	Collector power dissipation		$T_a=25^\circ\text{C}$	1.5	W
			$T_C=25^\circ\text{C}$	40	
T_j	Junction temperature			150	$^\circ\text{C}$
T_{stg}	Storage temperature			-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SB707	$I_C = -10mA; I_B = 0$	-60			V
		2SB708		-80			
V_{CEsat}	Collector-emitter saturation voltage		$I_C = -5A; I_B = -0.5 A$			-0.5	V
V_{BEsat}	Base-emitter saturation voltage		$I_C = -5A; I_B = -0.5 A$			-1.5	V
I_{CBO}	Collector cut-off current		$V_{CB} = -60V; I_E = 0$			-10	μA
I_{EBO}	Emitter cut-off current		$V_{EB} = -5V; I_C = 0$			-10	μA
h_{FE-1}	DC current gain		$I_C = -3A; V_{CE} = -1V$	40		200	
h_{FE-2}	DC current gain		$I_C = -5A; V_{CE} = -1V$	20			

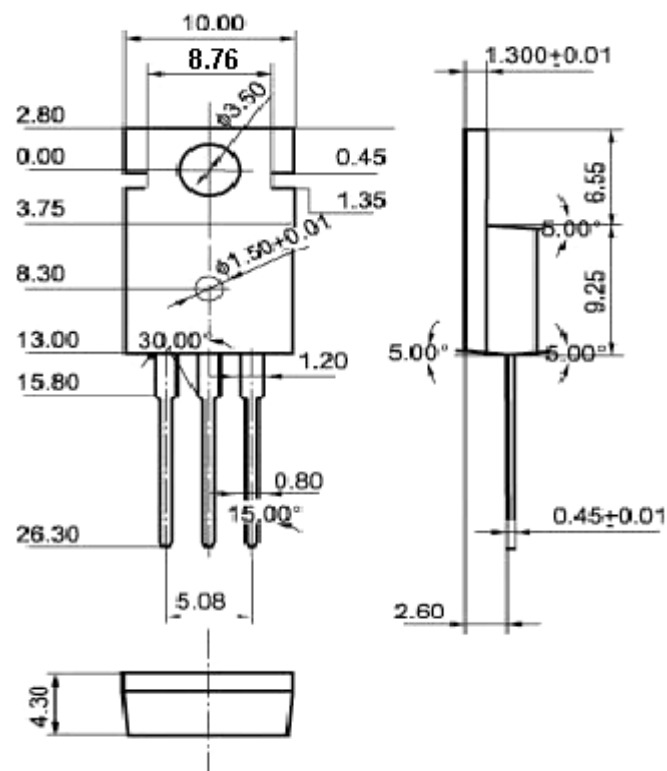
◆ h_{FE-2} classifications

R	O	Y
40-80	60-120	100-200

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PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)